

**Amendments to the Claims**

Claims 1-43 (Cancelled).

44. (Previously presented) A method of forming a dynamic random access memory (DRAM) comprising:

forming a plurality of conductive lines over a substrate having a memory array area and a peripheral area outward of the memory array area;

forming conductive material over the substrate comprising:

conductive plugs received over substrate node locations over which storage capacitors are to be formed within the memory array area, and

conductive material received over portions of some of the conductive lines within the peripheral area;

forming openings through an insulative material and exposing the conductive plugs within the memory array area and the conductive material within the peripheral area;

forming a storage capacitor electrode layer within the openings;

removing portions of the storage capacitor electrode layer within the memory array area sufficient to form a storage capacitor electrode within the memory array; and

entirely removing the storage capacitor electrode layer and at least some of the conductive material received over the conductive lines within the peripheral area and outwardly expose conductive portions of conductive lines within the peripheral area.

45. (Original) The method of claim 44, wherein the forming of the storage capacitor electrode layer comprises forming a cell plate layer within the openings.

46. (Original) The method of claim 44, wherein the forming of the storage capacitor electrode layer comprises forming a cell plate layer within the openings, and wherein the removing of the storage capacitor electrode layer comprises doing so in a common masking step.

47. (Original) The method of claim 44, wherein the forming of the storage capacitor electrode layer comprises forming a cell plate layer within the openings, and wherein the removing of the storage capacitor electrode layer comprises doing so in a common etching step.

48. (Original) The method of claim 44, wherein the forming of the storage capacitor electrode layer comprises forming a storage node layer within the openings.

49. (Original) The method of claim 44, wherein the forming of the storage capacitor electrode layer comprises forming a storage node layer within the openings, and wherein the removing of the storage capacitor electrode layer comprises doing so in multiple removing steps.

Claims 50-58. (Cancelled)